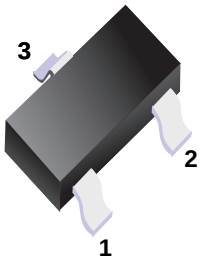
SL3906T

PNP Switching Transistor



1.Base
2.Emitter
3.Collector

■ Simplified outline(SOT-523)

■ Features

- Epitaxial Planar Die Construction
- Also Available in Lead Free Version
- Complementary to SL3904T

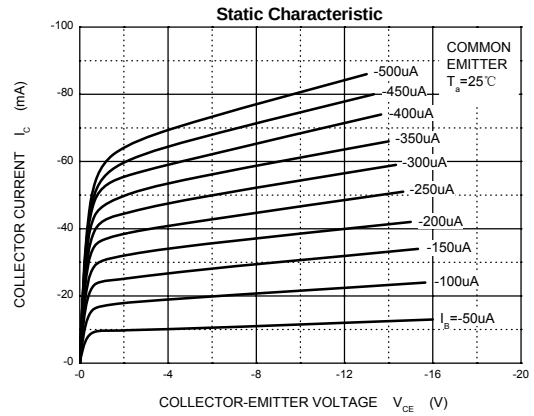
■ Absolute Maximum Ratings Ta = 25℃

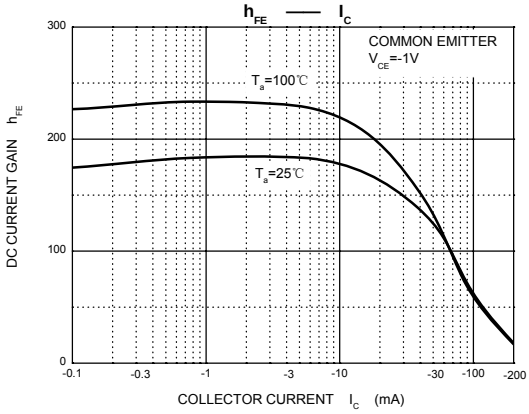
Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-40	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

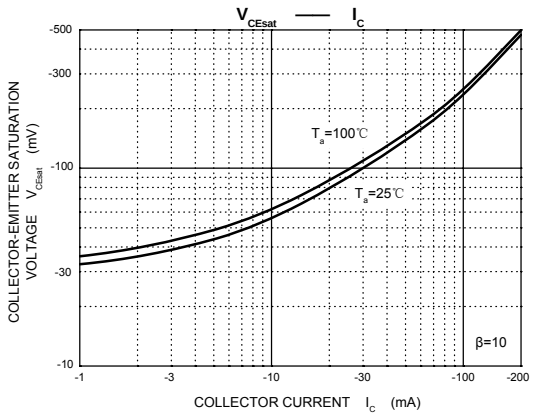
■ Electrical Characteristics Ta = 25℃

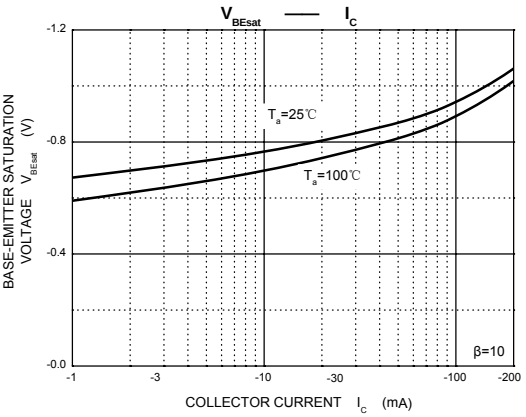
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA， I_E= 0	-40			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA， I_B= 0	-40			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A， I_C= 0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30 V , I_E= 0			-100	nA
Collector cut-off current	I_{CEX}	V_{CB}=-30V,$V_{BE(off)}$= 3V			-50	
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-1mA			-0.25	V
		I_C= -50 mA, I_B= -5mA			-0.4	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 mA, I_B=-1mA	-0.65		-0.85	
		I_C= -50 mA, I_B= -5mA			-0.95	
DC current gain	$h_{FE(1)}$	V_{CE}= -10V, I_C=- 0.1mA	60			
	$h_{FE(2)}$	V_{CE}= -10V, I_C= -1mA	80			
	$h_{FE(3)}$	V_{CE}= -10V, I_C=- 10mA	100		300	
	$h_{FE(4)}$	V_{CE}= -10V, I_C= -50mA	60			
	$h_{FE(5)}$	V_{CE}= -10V, I_C= -100mA	30			
Delay time	t_d	V_{CC}=-3V, $V_{BE(OFF)}$= 0.5V I_C=-10mA , I_{B1}=-1mA			35	nS
Rise time	t_r				35	
Storage time	t_s	V_{CC}=-3V, I_C=-10mA, I_{B1}=I_{B2}=-1mA			225	
Fall time	t_f				75	
Noise figure	NF	V_{CE}=-5V,Ic= -0.1mA			4	dB
Collector input capacitance	C_{ib}	V_{EB}= -0.5V, I_E= 0,f=1MHz			10	pF
Collector output capacitance	C_{ob}	V_{CB}= -5V, I_E= 0,f=1MHz			4.5	
Transition frequency	f_T	V_{CE}= -20V, I_C= -10mA,f=100MHz	250			MHz

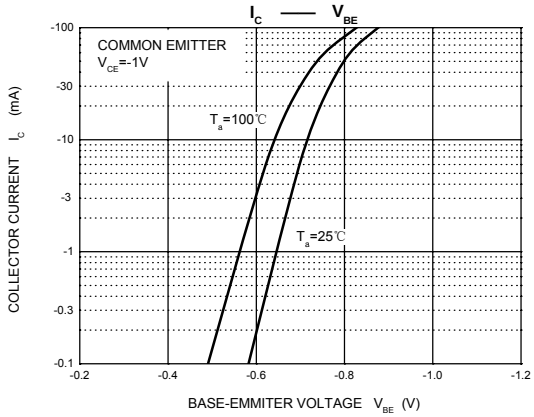
Typical Characterisitics

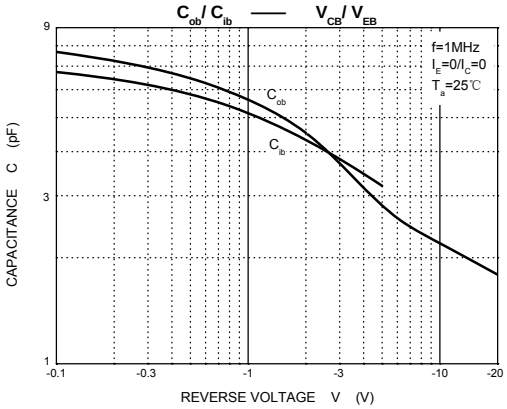


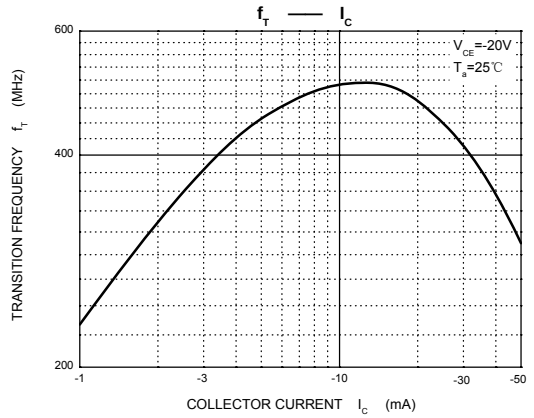


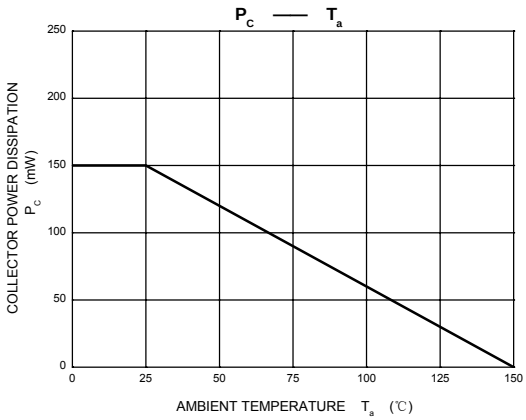




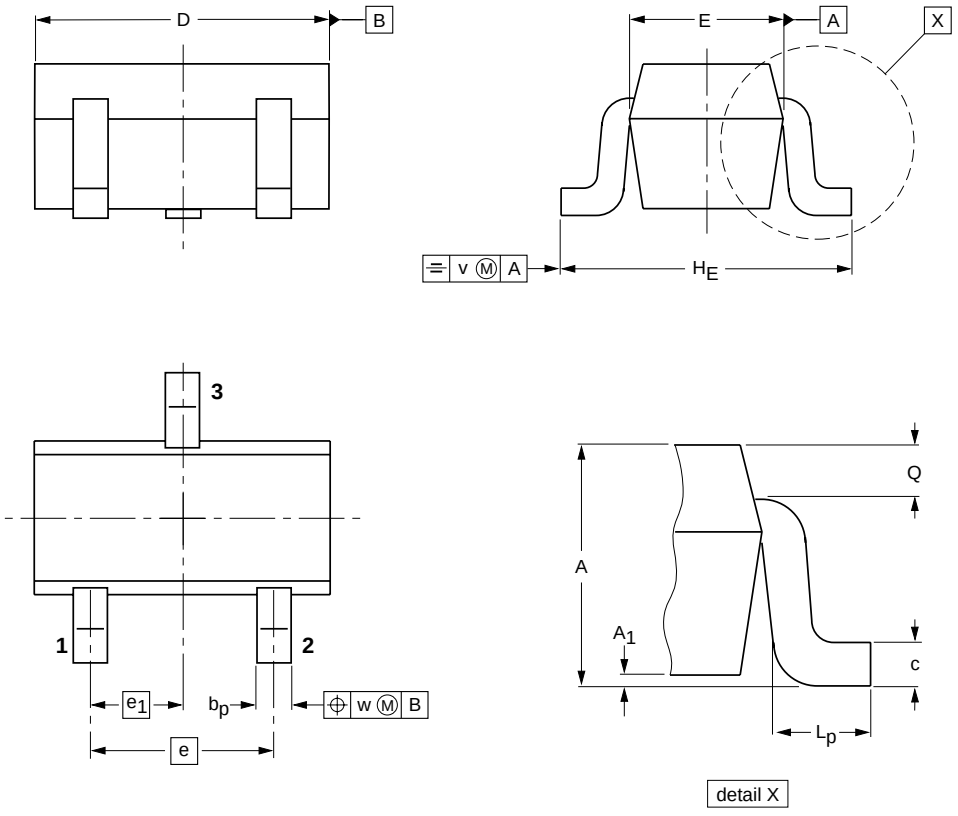








■ SOT-523



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

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